

**MAXIMUM RATINGS**

Rating	Symbol	BC 393	BC 394	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	180	180	V <sub>dc</sub>
Collector-Base Voltage	V <sub>CBO</sub>	180	180	V <sub>dc</sub>
Emitter-Base Voltage	V <sub>EBO</sub>	6	6	V <sub>dc</sub>
Collector Current - Continuous	I <sub>C</sub>	0.5		Amp
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	0.4	2.66	Watt mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C T <sub>C</sub> = 100°C Derate above 25°C	P <sub>D</sub>	1.5		Watt mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-65 to +200		°C

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	R <sub>θJC</sub>	125	°C/W

**BC393**

PNP

**BC394**

NPN

**CASE 22-03, STYLE 1  
TO-18 (TO-206AA)**
**HIGH VOLTAGE TRANSISTOR**
**4**
**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	180			V <sub>dc</sub>
Collector-Base Breakdown Voltage (I <sub>C</sub> = 100 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	180			V <sub>dc</sub>
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 100 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	6			V <sub>dc</sub>
Collector Cutoff Current (V <sub>CB</sub> = 100 V, I <sub>E</sub> = 0)	I <sub>CBO</sub>			50	nA
Collector-Emitter Cutoff (V <sub>CE</sub> = 100 V, I <sub>B</sub> = 0) (T <sub>Amb</sub> = 150°C)	I <sub>CEO</sub>			50	μA

**ON CHARACTERISTICS (1)**

DC Current Gain (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	50	100		
Collector-Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1 mAdc)	V <sub>CE(sat)</sub>		0.15	0.3	V <sub>dc</sub>
Base-Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1 mAdc)	V <sub>BE(sat)</sub>		0.7	0.9	V <sub>dc</sub>

**DYNAMIC CHARACTERISTICS**

Current Gain Bandwidth Product (I <sub>C</sub> = 20 mAdc, V <sub>CE</sub> = 20 Vdc, f = 20 MHz)	f <sub>T</sub>	50	110	200	MHz
Output Capacitance (I <sub>E</sub> = 0, V <sub>CB</sub> = 20 Vdc, f = 1 MHz)	C <sub>obo</sub>	—	3.5	7	pF
Input Capacitance (I <sub>C</sub> = 0, V <sub>EB</sub> = 0.5 Vdc, f = 1 MHz)	C <sub>ib</sub>	—	75	—	pF
Turn-On Time (I <sub>B1</sub> = 10 mA, I <sub>C</sub> = 50 mAdc, V <sub>CC</sub> = 100 Vdc)	t <sub>on</sub>	—	100	—	ns
Turn-Off Time (I <sub>B2</sub> = 10 mAdc, I <sub>C</sub> = 50 mAdc, V <sub>CC</sub> = 100 Vdc)	t <sub>off</sub>	—	400	—	ns

\* Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.